

P-Ch 30V Fast Switching MOSFETs

General Description

The QM3003M3 is the highest performance trench P-ch MOSFETs with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The QM3003M3 meet the RoHS and Green Product requirement , 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		10s	Steady State	
V_{DS}	Drain-Source Voltage	-30		V
V_{GS}	Gate-Source Voltage	± 20		V
$I_{D@T_C=25^{\circ}C}$	Continuous Drain Current, $V_{GS} @ -10V^1$	-32		A
$I_{D@T_C=100^{\circ}C}$	Continuous Drain Current, $V_{GS} @ -10V^1$	-20		A
$I_{D@T_A=25^{\circ}C}$	Continuous Drain Current, $V_{GS} @ -10V^1$	-12.2	-7.7	A
$I_{D@T_A=70^{\circ}C}$	Continuous Drain Current, $V_{GS} @ -10V^1$	-9.8	-6.2	A
I_{DM}	Pulsed Drain Current ²	-65		A
EAS	Single Pulse Avalanche Energy ³	176		mJ
I_{AS}	Avalanche Current	-38		A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation ⁴	29		W
$P_D@T_A=25^{\circ}C$	Total Power Dissipation ⁴	4.2	1.67	W
T_{STG}	Storage Temperature Range	-55 to 150		$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 150		$^{\circ}C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	75	$^{\circ}C/W$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹ (t ≤ 10s)	---	30	$^{\circ}C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	4.32	$^{\circ}C/W$

Product Summary

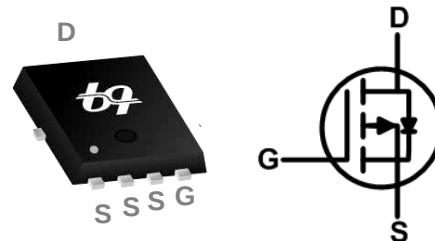


BVDSS	RDSON	ID
-30V	20mΩ	-32A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

PRPAK3X3 Pin Configuration



Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=-1mA$	---	-0.022	---	V/ $^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V, I_D=-15A$	---	16	20	m Ω
		$V_{GS}=-4.5V, I_D=-10A$	---	25	32	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.0	-1.5	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.6	---	mV/ $^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-24V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	-1	μA
		$V_{DS}=-24V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-5V, I_D=-15A$	---	19	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	---	13	26	Ω
Q_g	Total Gate Charge (-4.5V)	$V_{DS}=-15V, V_{GS}=-4.5V, I_D=-15A$	---	12.5	17.5	nC
Q_{gs}	Gate-Source Charge		---	5.4	7.6	
Q_{gd}	Gate-Drain Charge		---	5	7	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-15V, V_{GS}=-10V, R_G=3.3\Omega, I_D=-15A$	---	4.4	8.8	ns
T_r	Rise Time		---	11.2	20.2	
$T_{d(off)}$	Turn-Off Delay Time		---	34	68	
T_f	Fall Time		---	18	36	
C_{iss}	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V, f=1MHz$	---	1345	1883	pF
C_{oss}	Output Capacitance		---	194	272	
C_{rss}	Reverse Transfer Capacitance		---	158	221	

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy ⁵	$V_{DD}=-25V, L=0.1mH, I_{AS}=-20A$	49	---	---	mJ

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,6}	$V_G=V_D=0V$, Force Current	---	---	-32	A
I_{SM}	Pulsed Source Current ^{2,6}		---	---	-65	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	---	-1.2	V
t_{rr}	Reverse Recovery Time	$I_F=-15A, di/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	12.4	---	nS
Q_{rr}	Reverse Recovery Charge	$T_J=25^\circ\text{C}$	---	5	---	nC

Note :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
2. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. The EAS data shows Max. rating. The test condition is $V_{DD}=-25V, V_{GS}=-10V, L=0.1mH, I_{AS}=-38A$
4. The power dissipation is limited by 150°C junction temperature
5. The Min. value is 100% EAS tested guarantee.
6. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.

Typical Characteristics

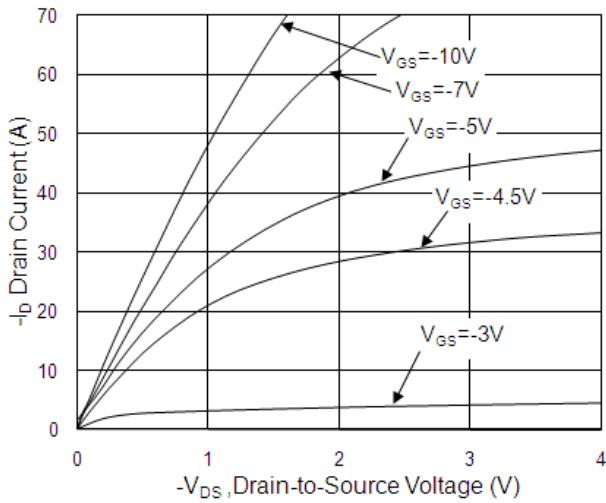


Fig.1 Typical Output Characteristics

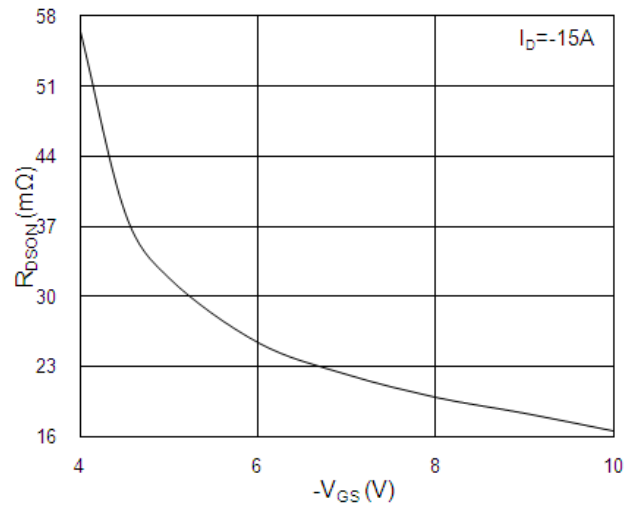


Fig.2 On-Resistance v.s Gate-Source

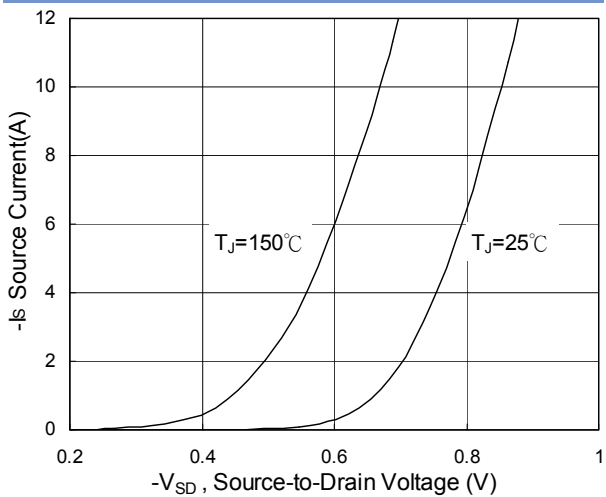


Fig.3 Forward Characteristics of Reverse

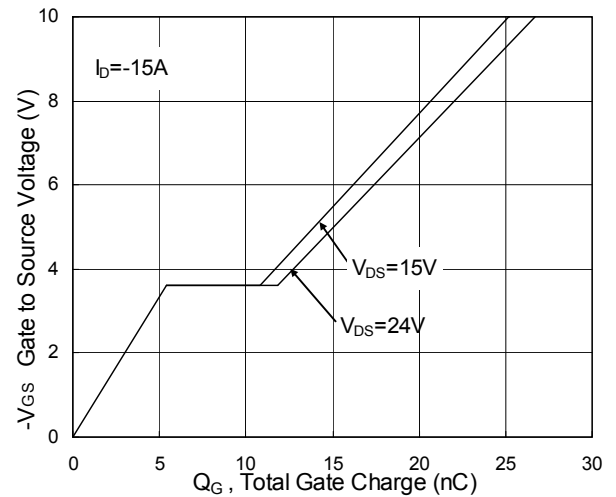


Fig.4 Gate-Charge Characteristics

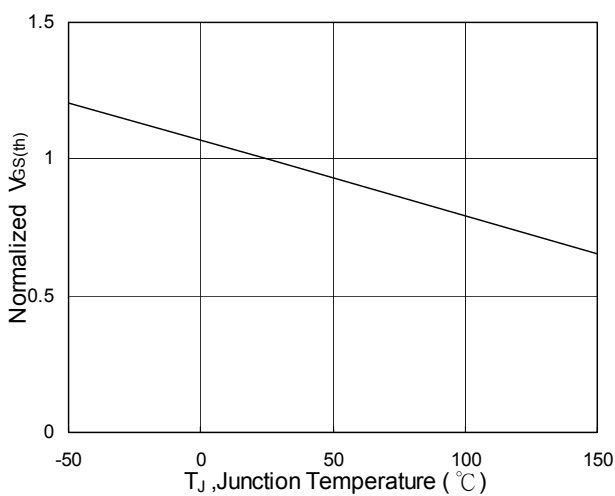


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

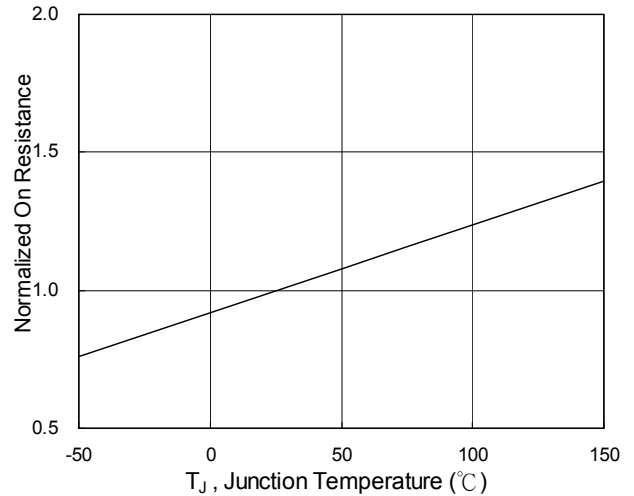


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

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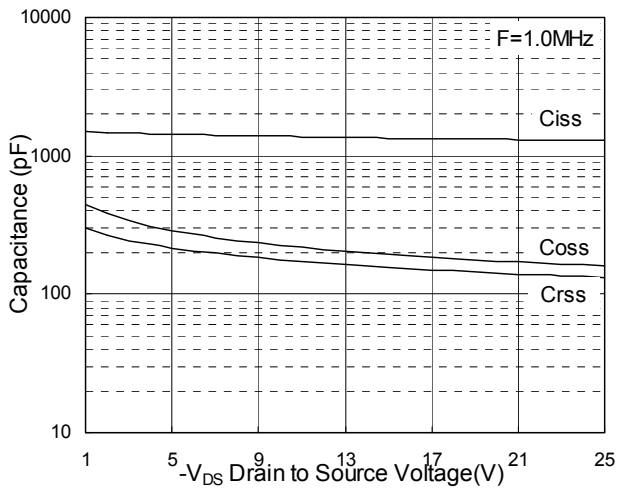


Fig.7 Capacitance

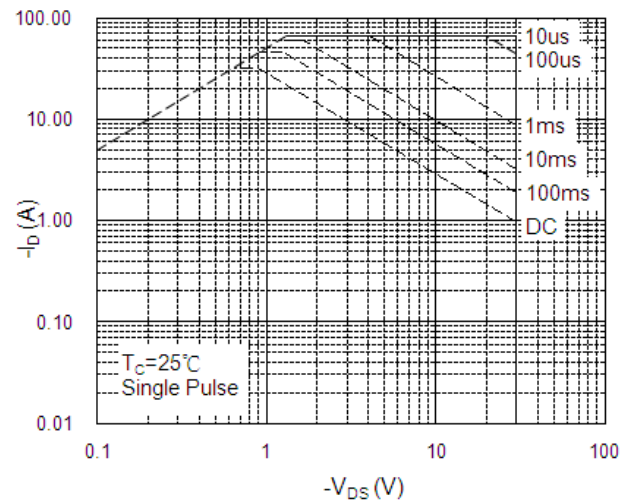


Fig.8 Safe Operating Area

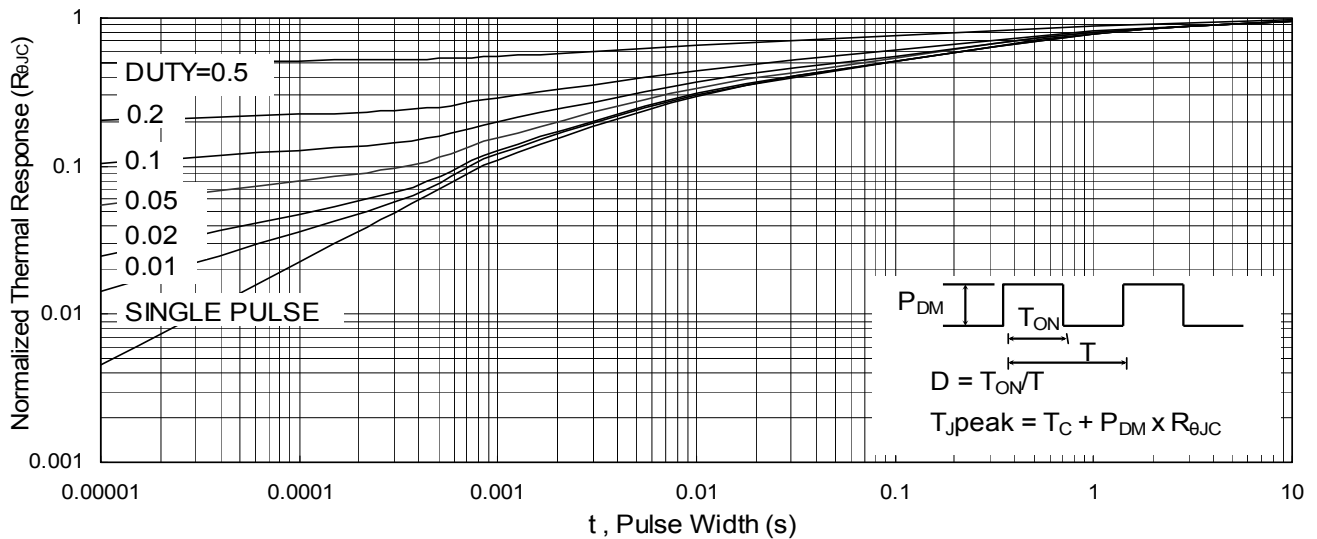


Fig.9 Normalized Maximum Transient Thermal Impedance

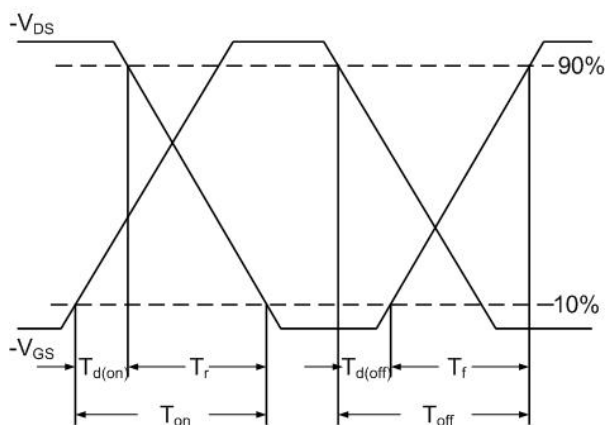


Fig.10 Switching Time Waveform

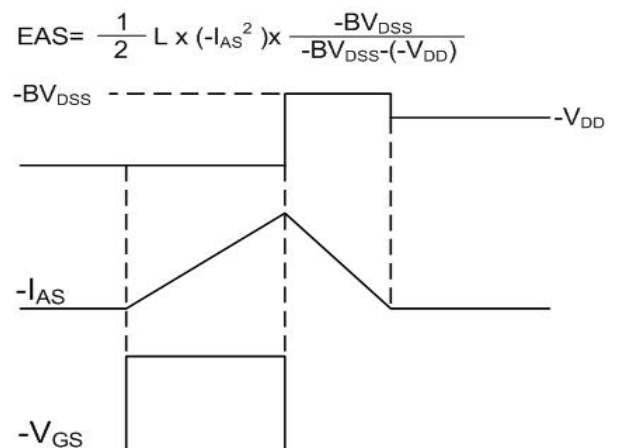


Fig.11 Unclamped Inductive Switching Waveform